

Stud Diode

Fast Recovery Rectifier Diode

SKN 3F20 SKR 3F20

Features

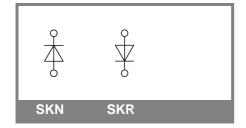
- · Small recovered charge
- Soft recovery
- Up to 1200 V reverse voltage
- Hermetic metal case with glass insulator
- Threaded stud ISO M5 or 10-32 UNF
- SKN: anode to stud SKR: cathode to stud

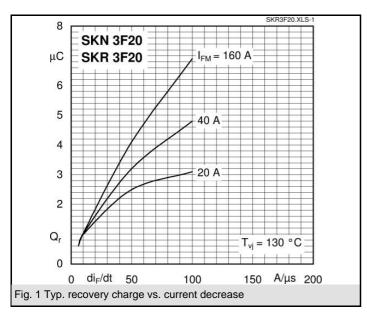
Typical Applications

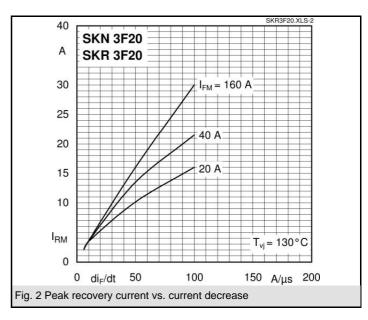
- Inverse diode for power transistor, GTO thyristor, asymmetric thyristor
- SMPS, inverters, choppers
- · for severe ambient conditions

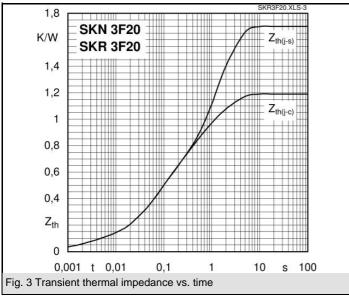
V_{RSM}	V_{RRM}	I _{FRMS} = 41 A (maximum value for continuous operation)		
V	V	I _{FAV} = 20 A (sin. 180; 5000 Hz; T _c = 104 °C)		
800	800	SKN 3F20/08	SKR 3F20/08	
800	800	SKN 3F20/08UNF	SKR 3F20/08UNF	
1000	1000	SKN 3F20/10	SKR 3F20/10	
1000	1000	SKN 3F20/10UNF	SKR 3F20/10UNF	
1200	1200	SKN 3F20/12	SKR 3F20/12	
1200	1200	SKN 3F20/12UNF	SKR 3F20/12UNF	

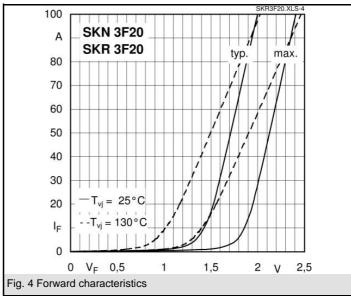
Symbol	Conditions	Values	Units
I _{FAV}	sin. 180; T _c = 85 (100) °C	26 (22)	Α
I_{FAV}	K5,5; T _a = 45 °C; sin. 180; 5000 Hz	10	Α
I _{FSM}	T _{vi} = 25 °C; 10 ms	375	Α
	T _{vi} = 150 °C; 10 ms	310	Α
i²t	T _{vj} = 25 °C; 8,3 10 ms	700	A²s
	T _{vj} = 150 °C; 8,3 10 ms	480	A²s
V _F	T _{vi} = 25 °C; I _F = 50 A	max. 2,15	V
$V_{(TO)}$	T _{vi} = 130 °C	max. 1,3	V
r _T	T _{vj} = 130 °C	max. 12	mΩ
I_{RD}	$T_{vj} = 25 ^{\circ}\text{C}; V_{RD} = V_{RRM}$	max. 0,2	mA
I_{RD}	T_{vj} = 130 °C; V_{RD} = V_{RRM}	max. 20	mA
Q _{rr}	T _{vi} = 130 °C, I _F = 50 A,	1,5	μC
I _{RM}	$-di/dt = 15 \text{ A/}\mu\text{s}, \text{ V}_{\text{R}} = 30 \text{ V}$	5	Α
t _{rr}		600	ns
E _{rr}		-	mJ
R _{th(j-c)}		1,2	K/W
R _{th(c-s)}		0,5	K/W
T_{vj}		- 40 + 150	°C
T _{stg}		- 55 + 150	°C
V _{isol}		-	V~
M_s	to heatsink	1,5	Nm
а		5 * 9,81	m/s²
m	approx.	7	g
Case		E 7	

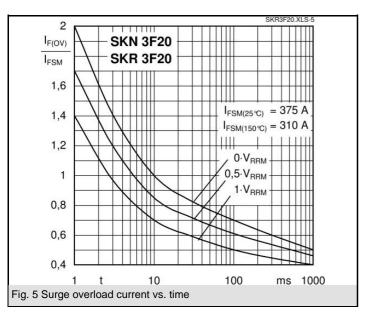


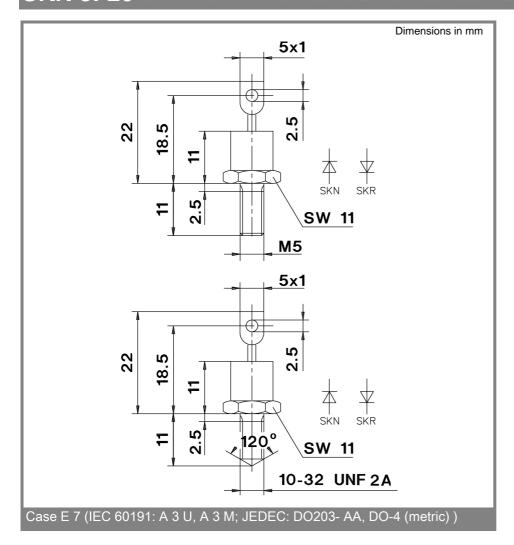












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